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| Application No. <u>09943199</u> | Prepared by <u>M. RUSTIA</u> | Tracking Number <u>05995539</u> | |
| Examiner-GAU <u>NELMB-2818</u> | Date <u>09-28-04</u> | Week Date <u>08-16-04</u> | |
| | No. of queries <u>1</u> | <u>VFW</u> | |

JACKET

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|----------------------|------------------------|--------------------|--------------------|
| a. Serial No. | f. Foreign Priority | k. Print Claim(s) | <u>p. PTO-1449</u> |
| b. Applicant(s) | g. Disclaimer | l. Print Fig. | q. PTOL-85b |
| c. Continuing Data | h. Microfiche Appendix | m. Searched Column | r. Abstract |
| d. PCT | i. Title | n. PTO-270/328 | s. Sheets/Figs |
| e. Domestic Priority | j. Claims Allowed | o. PTO-892 | t. Other |

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- g. Brief Description
- h. Sequence Listing
- i. Appendix
- j. Amendments
- k. Other

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| | | | Application Number | 09/943,199 | |
| | | | Filing Date | August 29, 2001 | |
| | | | First Named Inventor | Kristy A. Campbell | |
| | | | Art Unit | 2818 | |
| | | | Examiner Name | D. Vu | |
| Sheet | 1 | of | 5 | Attorney Docket Number | M4065.0704/P704 |

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| | | | Examiner Name | D. Vu | |
| Sheet | 2 | of | 5 | Attorney Docket Number | M4065.0704/P704 |

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PTO/SB/08A (10-01)

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| Application Number | 09/943,199 |
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| First Named Inventor | Kristy A. Campbell |
| Art Unit | 2818 |
| Examiner Name | D. Vu |
| Attorney Docket Number | M4065.0704/P704 |

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| Application Number | 09/943,199 |
| Filing Date | August 29, 2001 |
| First Named Inventor | Kristy A. Campbell |
| Art Unit | 2818 |
| Examiner Name | D. Vu |
| Attorney Docket Number | M4065.0704/P704 |

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|-------|---|----|---|
| Sheet | 4 | of | 5 |
|-------|---|----|---|

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| Examiner Name | D. Vu |

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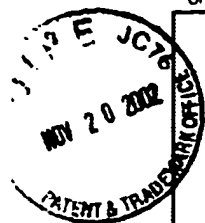
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